

Technische Information / Technical Information

IGBT-Module
IGBT-Modules

FF 800 R 12 KL4C

eupec



Höchstzulässige Werte / Maximum rated values

Elektrische Eigenschaften / Electrical properties

Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauerstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	800	A
	$T_C = 25^\circ\text{C}$	I_C	1250	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_P = 1\text{ ms}, T_C = 80^\circ\text{C}$	I_{CRM}	1600	A
Gesamt-Verlustleistung total power dissipation	$T_C=25^\circ\text{C}$, Transistor	P_{tot}	5,0	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Dauerstrom DC forward current		I_F	800	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_P = 1\text{ ms}$	I_{FRM}	1600	A
Grenzlastintegral der Diode I^2t - value, Diode	$V_R = 0V, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	I^2t	140	kA^2s
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	V_{ISOL}	2,5	kV

Charakteristische Werte / Characteristic values

Transistor / Transistor

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 800A, V_{GE} = 15V, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,1	2,6	V
	$I_C = 800A, V_{GE} = 15V, T_{vj} = 125^\circ\text{C}$		-	2,4	2,9	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 32\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15V...+15V$	Q_G	-	8,6	-	μC
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25V, V_{GE} = 0V$	C_{ies}	-	56	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25V, V_{GE} = 0V$	C_{res}	-	3,6	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200V, V_{GE} = 0V, T_{vj} = 25^\circ\text{C}$	I_{CES}	-	0,02	1,5	mA
	$V_{CE} = 1200V, V_{GE} = 0V, T_{vj} = 125^\circ\text{C}$		-	1	-	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0V, V_{GE} = 20V, T_{vj} = 25^\circ\text{C}$	I_{GES}	-	-	600	nA

prepared by: Mark Münzer

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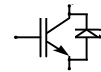
revision: 2

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Charakteristische Werte / Characteristic values

Transistor / Transistor

			min.	typ.	max.	
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 800A, V_{CE} = 600V$	$t_{d,on}$	-	0,27	-	μs
	$V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 25^\circ C$ $V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 125^\circ C$		-	0,29	-	μs
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 800A, V_{CE} = 600V$	t_r	-	0,16	-	μs
	$V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 25^\circ C$ $V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 125^\circ C$		-	0,17	-	μs
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 800A, V_{CE} = 600V$	$t_{d,off}$	-	1	-	μs
	$V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 25^\circ C$ $V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 125^\circ C$		-	1,1	-	μs
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 800A, V_{CE} = 600V$	t_f	-	0,1	-	μs
	$V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 25^\circ C$ $V_{GE} = \pm 15V, R_G = 1,8\Omega, T_{vj} = 125^\circ C$		-	0,11	-	μs
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 800A, V_{CE} = 600V, V_{GE} = 15V$ $R_G = 1,8\Omega, T_{vj} = 125^\circ C, L_S = 70nH$	E_{on}	-	120	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 800A, V_{CE} = 600V, V_{GE} = 15V$ $R_G = 1,8\Omega, T_{vj} = 125^\circ C, L_S = 70nH$	E_{off}	-	130	-	mWs
Kurzschlußverhalten SC Data	$t_P \leq 10\mu sec, V_{GE} \leq 15V, R_G = 1,8\Omega$ $T_{vj} \leq 125^\circ C, V_{CC} = 900V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	I_{SC}	-	5300	-	A
Modulinduktivität stray inductance module		L_{sCE}	-	20	-	nH
Modul Leitungswiderstand, Anschlüsse – Chip module lead resistance, terminals – chip	$T_C = 25^\circ C$	R_{CC+EE}	-	0,18	-	m Ω

Charakteristische Werte / Characteristic values

Diode / Diode

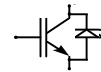
			min.	typ.	max.	
Durchlaßspannung forward voltage	$I_F = 800A, V_{GE} = 0V, T_{vj} = 25^\circ C$	V_F	-	1,8	2,3	V
	$I_F = 800A, V_{GE} = 0V, T_{vj} = 125^\circ C$		-	1,7	2,2	V
Rückstromspitze peak reverse recovery current	$I_F = 800A, -di_F/dt = 5700A/\mu sec$	I_{RM}	-	420	-	A
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$ $V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$		-	710	-	A
Sperrverzögerungsladung recovered charge	$I_F = 800A, -di_F/dt = 5700A/\mu sec$	Q_r	-	73	-	μAs
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$ $V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$		-	170	-	μAs
Abschaltenergie pro Puls reverse recovery energy	$I_F = 800A, -di_F/dt = 5700A/\mu sec$	E_{rec}	-	25	-	mWs
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$ $V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$		-	60	-	mWs

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Thermische Eigenschaften / Thermal properties

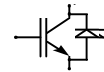
			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor, DC, pro Modul / per module	R_{thJC}	-	-	0,0125	K/W
	Transistor, DC, pro Zweig / per arm		-	-	0,0250	K/W
	Diode/Diode, DC, pro Modul / per module		-	-	0,0210	K/W
	Diode/Diode, DC, pro Zweig / per arm		-	-	0,0420	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module	R_{thCK}	-	0,006	-	K/W
	pro Zweig / per arm; $\lambda_{Paste} / \lambda_{grease} = 1 \text{ W/m} \cdot \text{K}$		-	0,012	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature		T_{op}	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see appendix						
Innere Isolation internal insulation				Al_2O_3		
Kriechstrecke creepage distance				17		mm
Luftstrecke clearance				10		mm
CTI comperative tracking index				275		
Anzugsdrehmoment f. mech. Befestigung mounting torque		M1	4,25	5	5,75	Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque		M2	1,7	2	2,3	Nm
	terminals M4 terminals M8		8		10	Nm
Gewicht weight		G		1500		g

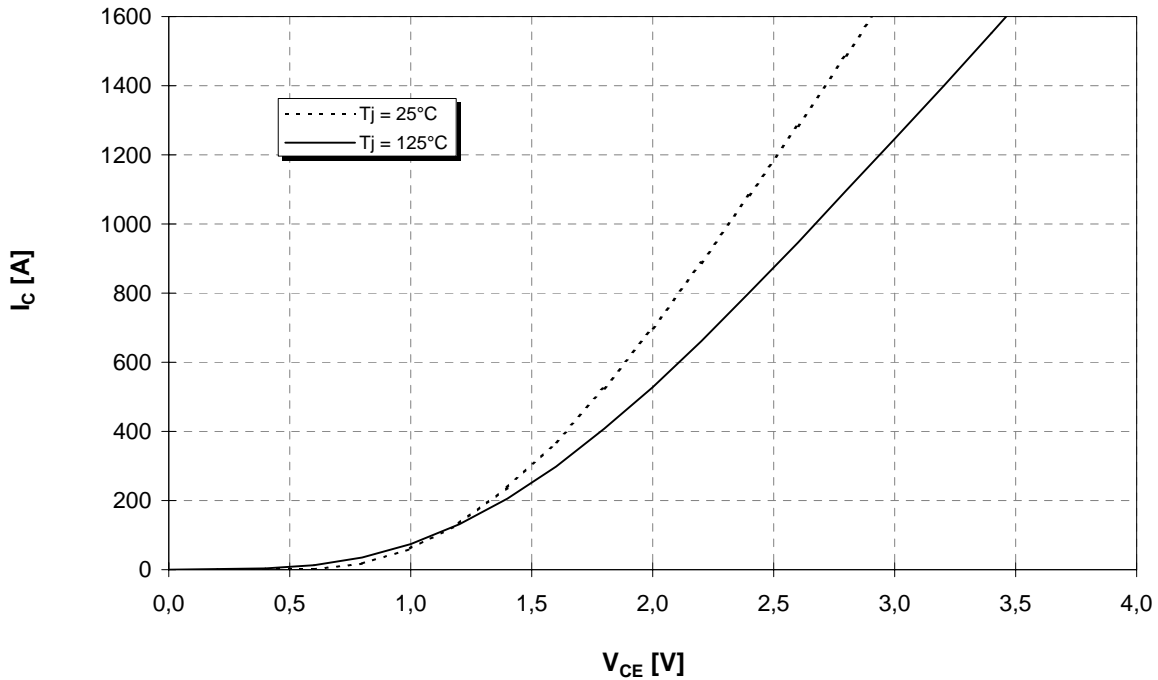
Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert.
Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



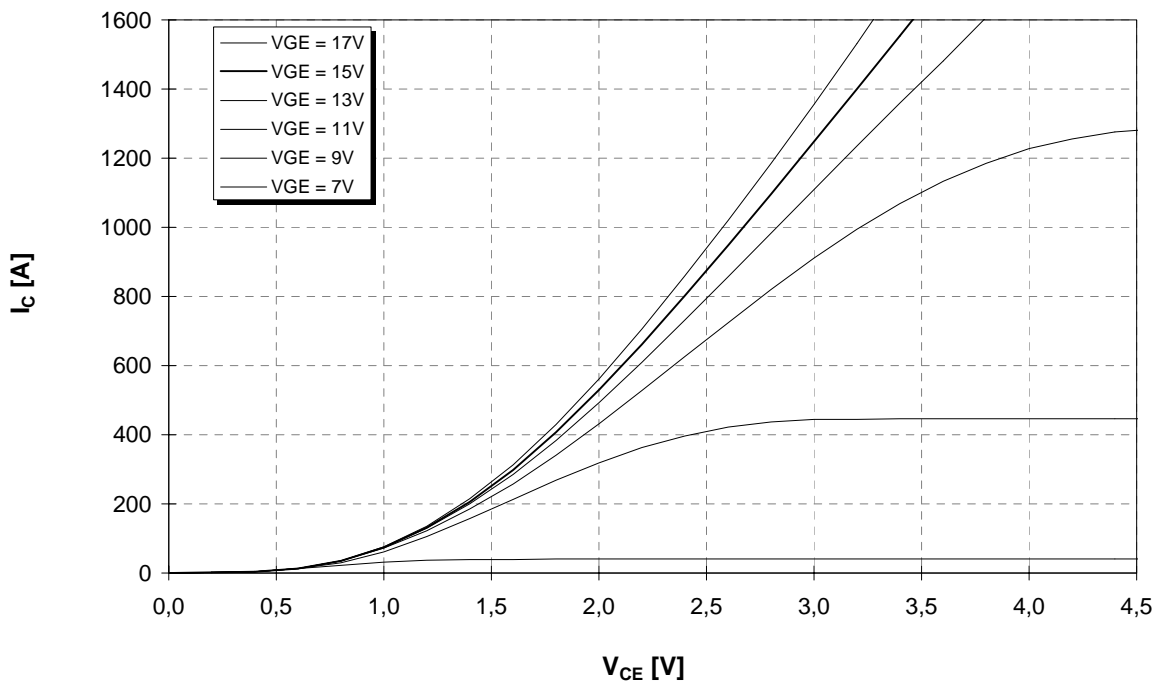
Ausgangskennlinie (typisch)
Output characteristic (typical)

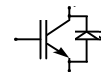
$I_c = f(V_{CE})$
 $V_{GE} = 15V$



Ausgangskennlinienfeld (typisch)
Output characteristic (typical)

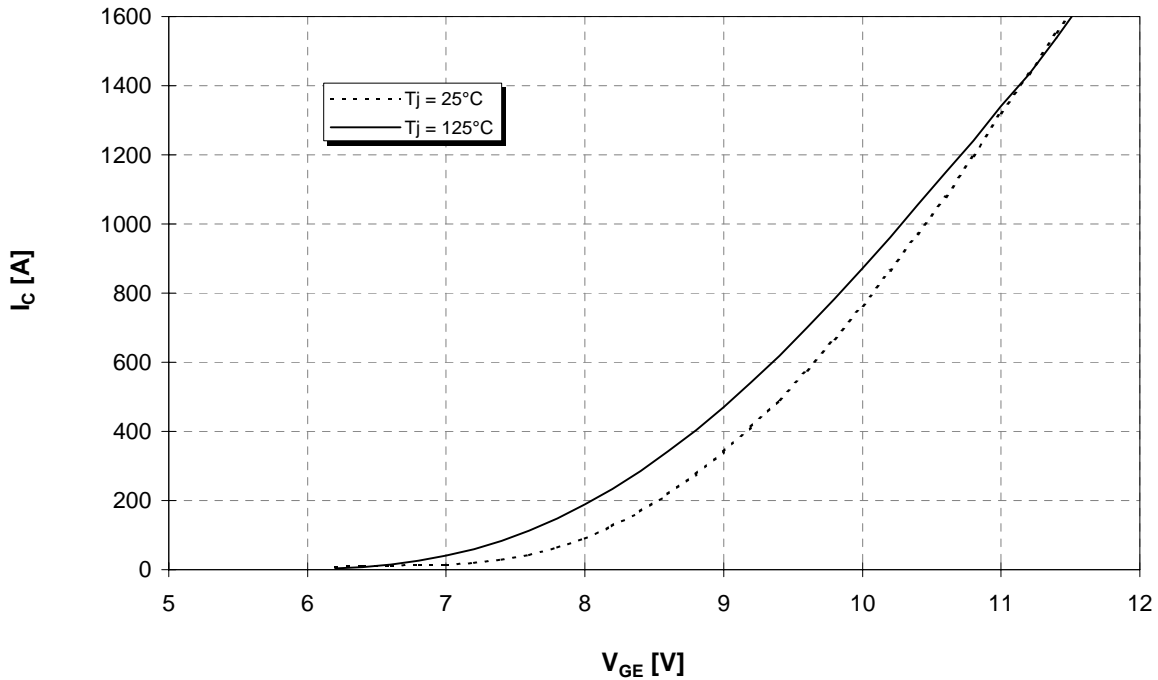
$I_c = f(V_{CE})$
 $T_{vj} = 125°C$





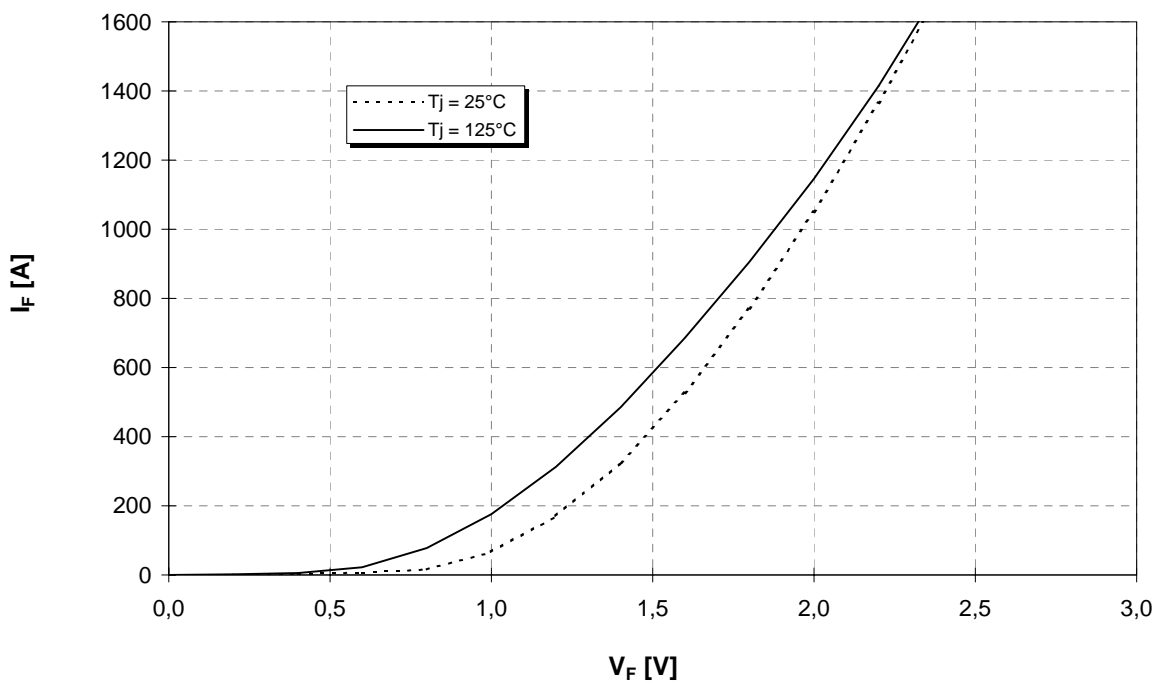
Übertragungscharakteristik (typisch)
Transfer characteristic (typical)

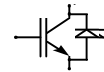
$I_c = f(V_{GE})$
 $V_{CE} = 20V$



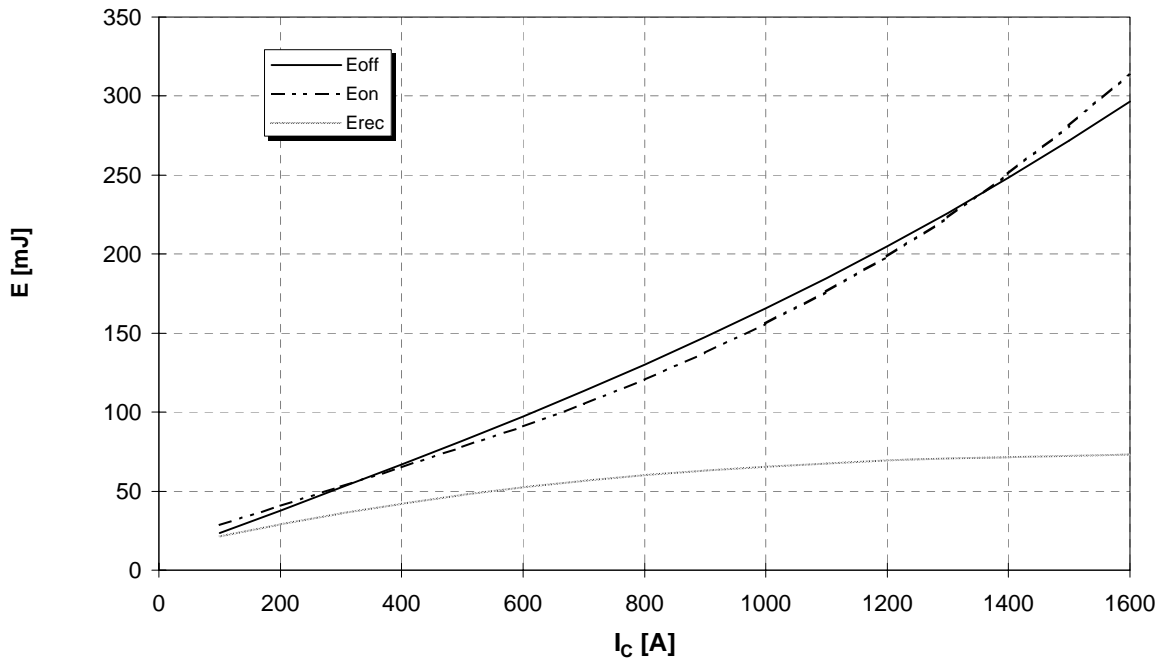
Durchlaßkennlinie der Inversdiode (typisch)
Forward characteristic of inverse diode (typical)

$I_F = f(V_F)$

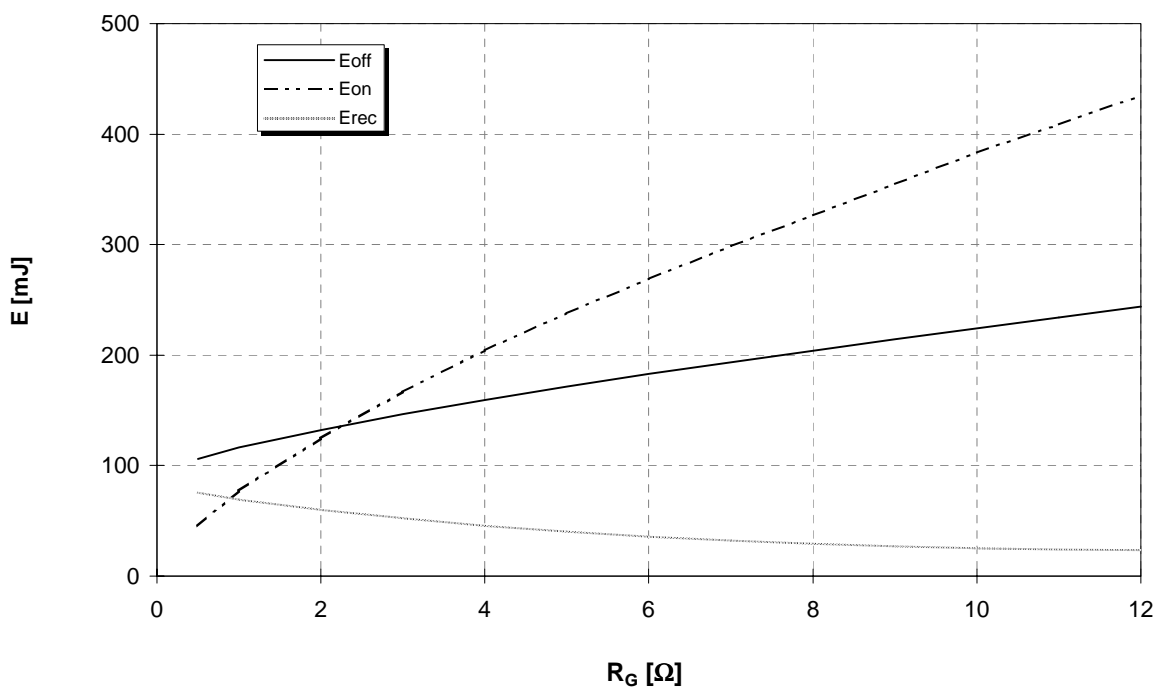


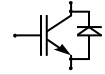


Schaltverluste (typisch) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$
Switching losses (typical) $V_{GE} = \pm 15V$, $R_{gon} = R_{goff} = 1,8 \Omega$, $V_{CE} = 600V$, $T_j = 125^\circ C$



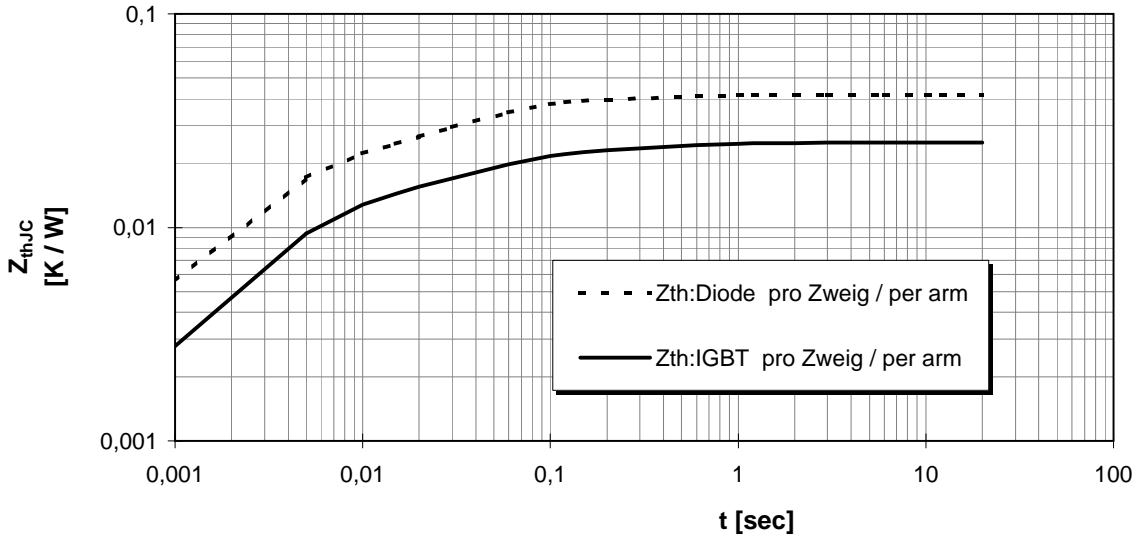
Schaltverluste (typisch) $E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$
Switching losses (typical) $V_{GE} = \pm 15V$, $I_C = 600A$, $V_{CE} = 600V$, $T_j = 125^\circ C$





Transienter Wärmewiderstand
Transient thermal impedance

$Z_{thJC} = f(t)$

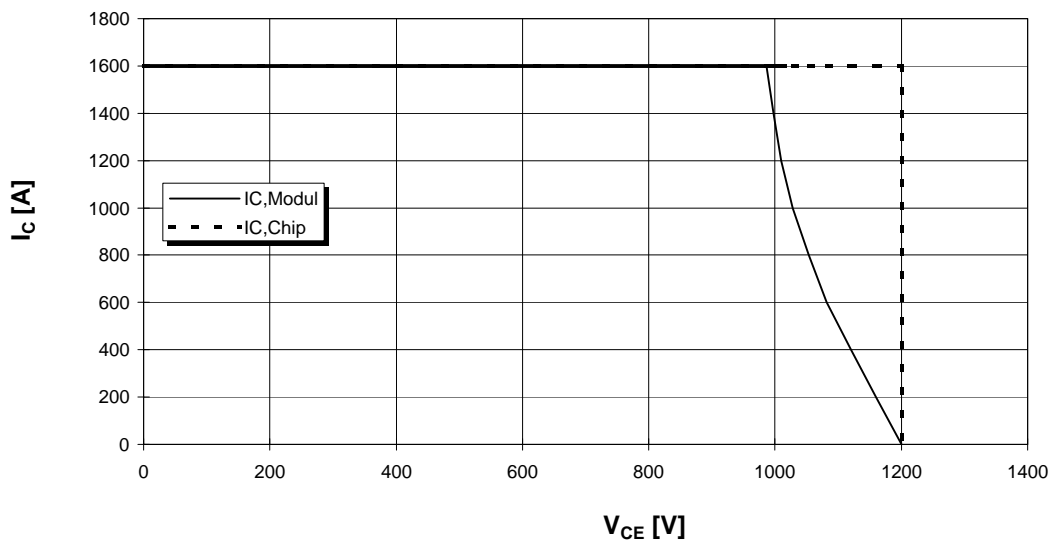


i	1	2	3	4
r_i [K/kW] : IGBT	11,4	9,9	1,7	1,9
τ_i [sec] : IGBT	0,004	0,04	0,19	0,5
r_i [K/kW] : Diode	17,9	9,8	11,3	3
τ_i [sec] : Diode	0,003	0,03	0,05	0,5

Sicherer Arbeitsbereich (RBSOA)

Reverse bias safe operation area (RBSOA)

$V_{GE} = \pm 15V, R_g = 1,80\Omega, T_{vj} = 125^\circ C$



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